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Kind regards,

Team Nexperia

1. General description

PNP general-purpose transistor in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: BC846BMB.

2. Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

3. Applications

- General-purpose switching and amplification
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	220	-	475	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	1 🔲	3
2	Е	emitter	2 3	1—
3	С	collector	Transparent top view	2
			DFN1006B-3 (SOT883B)	sym013





60 V, 100 mA PNP general-purpose transistor

6. Ordering information

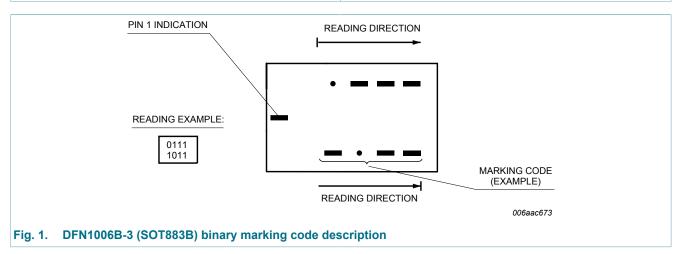
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BC856BMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

7. Marking

Table 4. Marking codes

Type number	Marking code
BC856BMB	0101 1010



60 V, 100 mA PNP general-purpose transistor

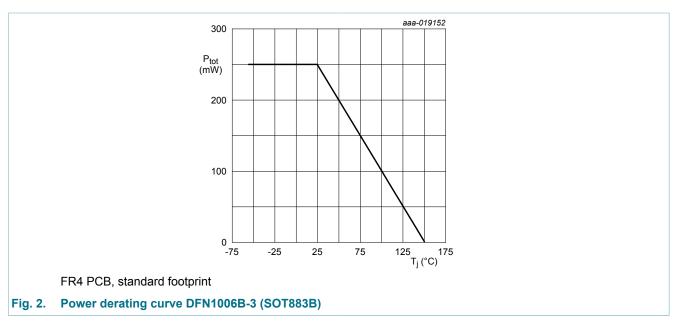
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-200	mA
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



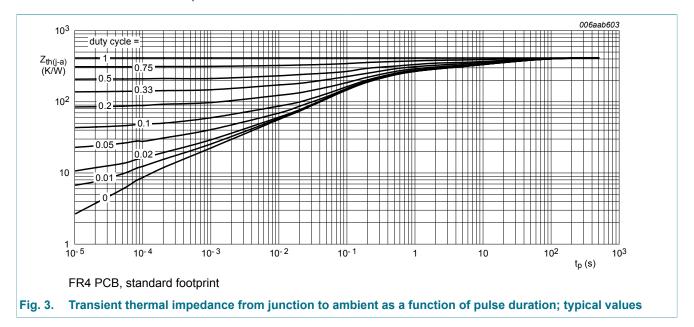
60 V, 100 mA PNP general-purpose transistor

Thermal characteristics

Thermal characteristics Table 6.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



4/12

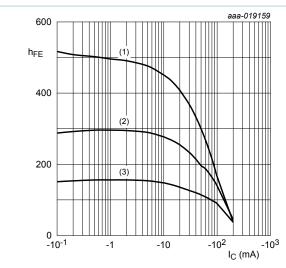
60 V, 100 mA PNP general-purpose transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-15	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	220	-	475	
V _{CEsat}	collector-emitter	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-	-200	mV
saturation voltage	I_C = -100 mA; I_B = -5 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-	-400	mV	
V _{BEsat} base-emitter sat voltage	base-emitter saturation	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-700	-	mV
	voltage	I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C	-	-850	-	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	-600	-	-750	mV
		V_{CE} = -5 V; I_{C} = -10 mA; T_{amb} = 25 °C	-	-	-820	mV
C _C	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	2.5	pF
C _E	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	4.5	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
NF	noise figure	V_{CE} = -5 V; I_{C} = -200 μ A; R_{S} = 2 $k\Omega$; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C	-	-	10	dB

60 V, 100 mA PNP general-purpose transistor



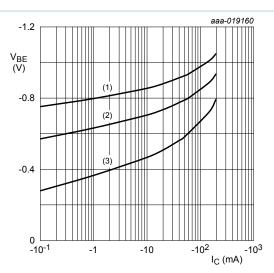
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



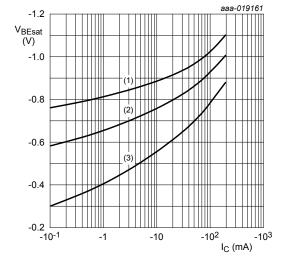
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



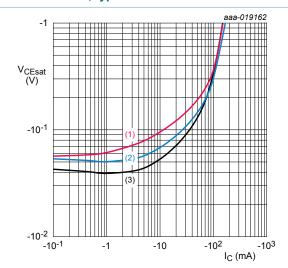
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150^{\circ}C$$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

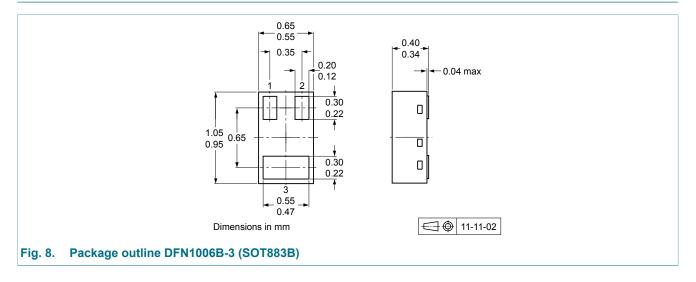
60 V, 100 mA PNP general-purpose transistor

11. Test information

11.1 Quality information

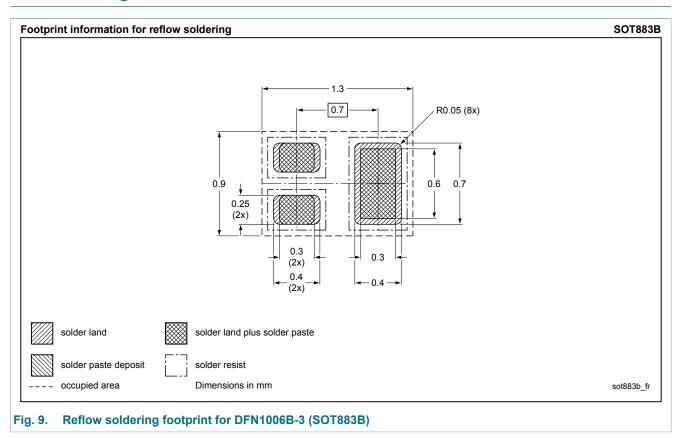
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



60 V, 100 mA PNP general-purpose transistor

13. Soldering



60 V, 100 mA PNP general-purpose transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC856BMB v.1	20150819	Product data sheet	-	-

60 V, 100 mA PNP general-purpose transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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60 V, 100 mA PNP general-purpose transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	1
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	7
11.1	Quality information	7
12	Package outline	7
13	Soldering	8
14	Revision history	9
15	Legal information	10
15.1	Data sheet status	10
15.2	Definitions	10
15.3	Disclaimers	10
15.4	Trademarks	11

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